

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

New York, New York

Makoto INAI, et al.

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Serial No.: To Be Assigned

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For: **FIELD-EFFECT SEMICONDUCTOR DEVICE**

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Assistant Commissioner for Patents
Washington, D.C. 20231-9999

PRELIMINARY AMENDMENT

Sir:

Please amend the above-identified application prior to examination, as follows:

IN THE CLAIMS:

Please amend claim 3 as follows:

3. (Amended) A field-effect semiconductor device according to claim [3] 2, wherein the channel layer and the semiconductor structure at the first junction face each have a dopant concentration of $1 \times 10^{18} \text{ cm}^{-3}$, and the contact layer and the semiconductor structure at the second junction face each have a dopant concentration of $1 \times 10^{18} \text{ cm}^{-3}$.

REMARKS

Claim 3 has been amended to correct a typographical error.